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May 2014

FDMS7608S

Dual N-Channel PowerTrench® MOSFET
Q1: 30 V, 22 A, 10.0 mΩ Q2: 30 V, 30 A, 6.3 mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 10.0 mΩ at V_{GS} = 10 V, I_D = 12 A
- Max $r_{DS(on)}$ = 13.6 mΩ at V_{GS} = 4.5 V, I_D = 10 A

Q2: N-Channel

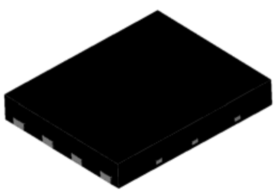
- Max $r_{DS(on)}$ = 6.3 mΩ at V_{GS} = 10 V, I_D = 15 A
- Max $r_{DS(on)}$ = 7.2 mΩ at V_{GS} = 4.5 V, I_D = 13 A
- RoHS Compliant

General Description

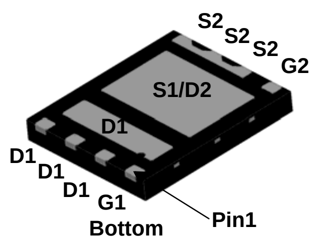
This device includes two specialized N-Channel MOSFETs in a dual MLP package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET™ (Q2) have been designed to provide optimal power efficiency.

Applications

- Computing
- Communications
- General Purpose Point of Load
- Notebook VCORE

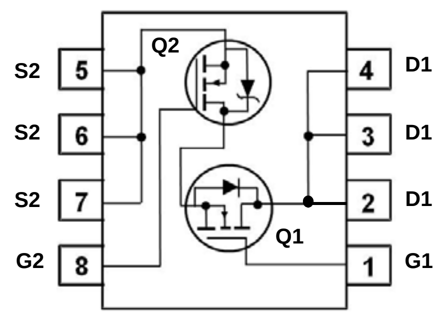


Top



Bottom

Power 56



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		30	30	V
V_{GS}	Gate to Source Voltage	(Note 3)	±20	±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25 °C	22	30	A
	-Continuous	T_A = 25 °C	12[1a]	15[1b]	
	-Pulsed		50	60	
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	29	33	mJ
P_D	Power Dissipation for Single Operation	T_A = 25°C	2.2[1a]	2.5[1b]	W
	Power Dissipation for Single Operation	T_A = 25°C	1.0[1c]	1.0[1d]	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	57[1a]	50[1b]	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125[1c]	120[1d]	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.0	3.2	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7608S	FDMS7608S	Power 56	13 ”	12 mm	3000 units

Electrical Characteristics $T_J = 25°C$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu A$, $V_{GS} = 0\ V$ $I_D = 1\ mA$, $V_{GS} = 0\ V$	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu A$, referenced to 25°C $I_D = 10\ mA$, referenced to 25°C	Q1 Q2		13 19		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\ V$, $V_{GS} = 0\ V$	Q1 Q2			1 500	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = 20\ V$, $V_{DS} = 0\ V$	Q1 Q2			100 100	nA nA

On Characteristics

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu A$ $V_{GS} = V_{DS}$, $I_D = 1\ mA$	Q1 Q2	1.2 1.2	1.9 1.7	3.0 3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu A$, referenced to 25°C $I_D = 10\ mA$, referenced to 25°C	Q1 Q2		-6 -4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ V$, $I_D = 12\ A$ $V_{GS} = 4.5\ V$, $I_D = 10\ A$ $V_{GS} = 10\ V$, $I_D = 12\ A$, $T_J = 125°C$	Q1		7.4 10.0 10.3	10.0 13.6 13.9	mΩ
		$V_{GS} = 10\ V$, $I_D = 15\ A$ $V_{GS} = 4.5\ V$, $I_D = 13\ A$ $V_{GS} = 10\ V$, $I_D = 15\ A$, $T_J = 125°C$	Q2		4.8 6.0 6.6	6.3 7.2 8.6	
g_{FS}	Forward Transconductance	$V_{DD} = 5\ V$, $I_D = 12\ A$ $V_{DD} = 5\ V$, $I_D = 15\ A$	Q1 Q2		54 76		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
C_{iss}	Input Capacitance	Q1: $V_{DS} = 15\ V$, $V_{GS} = 0\ V$, f = 1 MHZ Q2: $V_{DS} = 15\ V$, $V_{GS} = 0\ V$, f = 1 MHZ	Q1 Q2		1135 1380	1510 1835	pF
C_{oss}	Output Capacitance		Q1 Q2		390 478	520 635	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		42 60	65 90	pF
R_g	Gate Resistance		Q1 Q2	0.2 0.2	1.6 0.5	3.2 2.0	Ω

Switching Characteristics

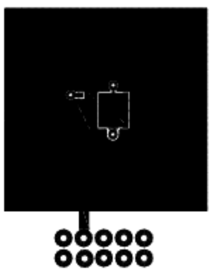
Symbol	Parameter	Test Conditions		Type	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	Q1 $V_{DD} = 15\ V$, $I_D = 12\ A$, $R_{GEN} = 6\ \Omega$ Q2 $V_{DD} = 15\ V$, $I_D = 15\ A$, $R_{GEN} = 6\ \Omega$		Q1 Q2		7 7	14 14	ns
t_r	Rise Time			Q1 Q2		3 3	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time			Q1 Q2		19 20	35 36	ns
t_f	Fall Time			Q1 Q2		3 2	10 10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0V to 10 V	Q1 $V_{DD} = 15\ V$, $I_D = 12\ A$ Q2 $V_{DD} = 15\ V$, $I_D = 15\ A$	Q1 Q2		18 21	24 30	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0V to 5 V		Q1 Q2		9 12	14 16	nC
Q_{gs}	Gate to Source Charge			Q1 Q2		3.6 3.5		nC
Q_{gd}	Gate to Drain “Miller” Charge			Q1 Q2		2.5 3.0		nC

Electrical Characteristics T_J = 25°C unless otherwise noted

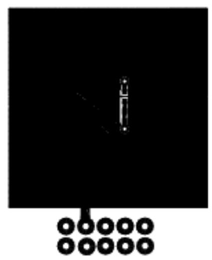
Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2 A (Note 2) V_{GS} = 0 V, I_S = 12 A (Note 2) V_{GS} = 0 V, I_S = 2 A (Note 2) V_{GS} = 0 V, I_S = 15 A (Note 2)	Q1 Q1 Q2 Q2		0.75 0.84 0.63 0.80	1.1 1.2 0.8 1.2	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 12 A, di/dt = 100 A/μs	Q1 Q2		25 21	40 34	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = 15 A, di/dt = 300 A/μs	Q1 Q2		9 19	18 33	nC

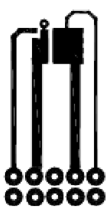
Notes:
1.$R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



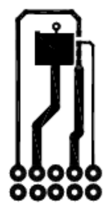
a. 57 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper



c. 125 °C/W when mounted on a minimum pad of 2 oz copper



d. 120 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

4. Q1: E_{AS} of 29 mJ is based on starting T_J = 25 °C; N-ch: L = 0.3 mH, I_{AS} = 14 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% tested at L = 3 mH, I_{AS} = 3.75 A.

Q2: E_{AS} of 33 mJ is based on starting T_J = 25 °C; N-ch: L = 0.3 mH, I_{AS} = 15 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% tested at L = 3 mH, I_{AS} = 3.9 A.

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

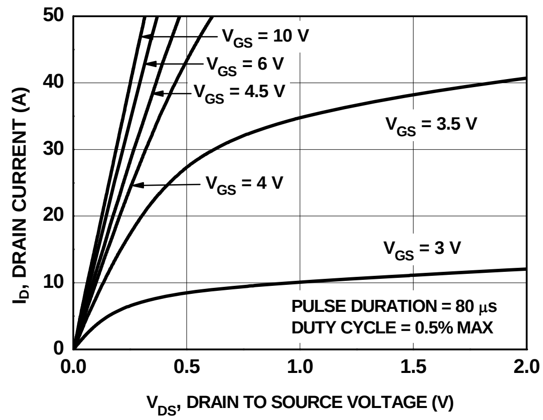


Figure 1. On Region Characteristics

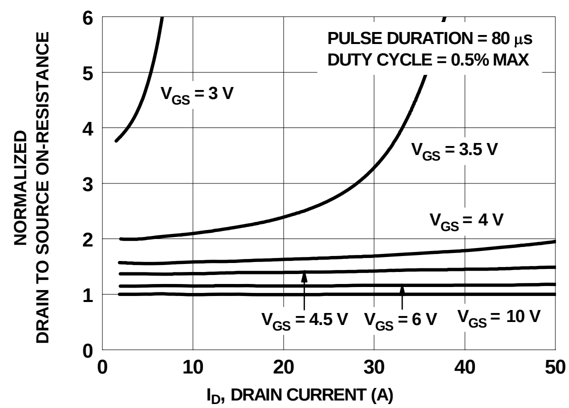


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

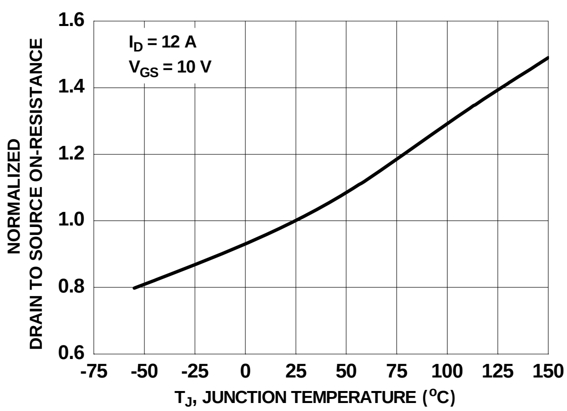


Figure 3. Normalized On Resistance vs Junction Temperature

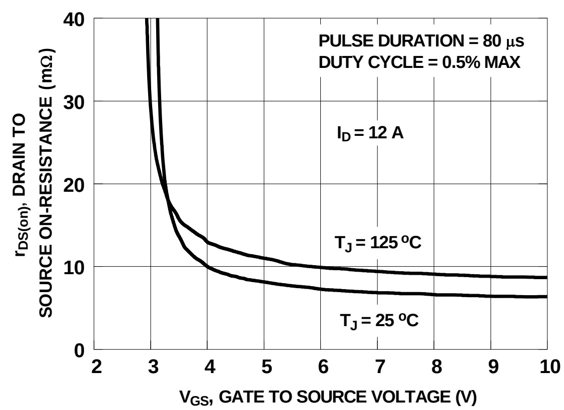


Figure 4. On-Resistance vs Gate to Source Voltage

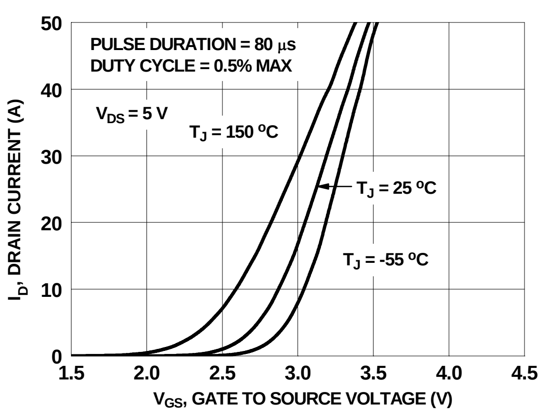


Figure 5. Transfer Characteristics

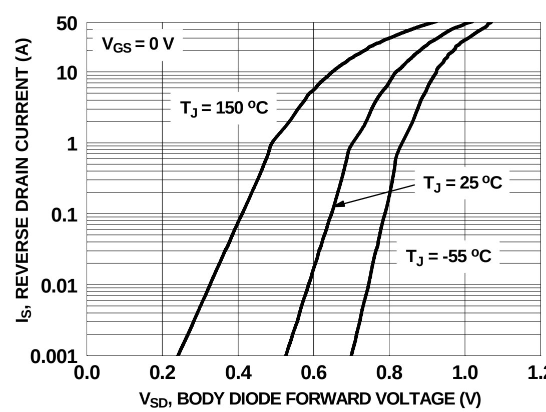


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

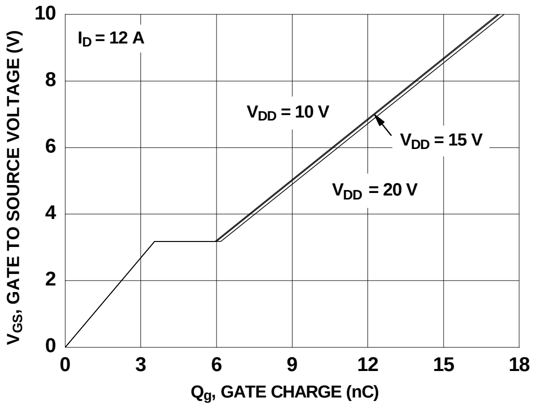


Figure 7. Gate Charge Characteristics

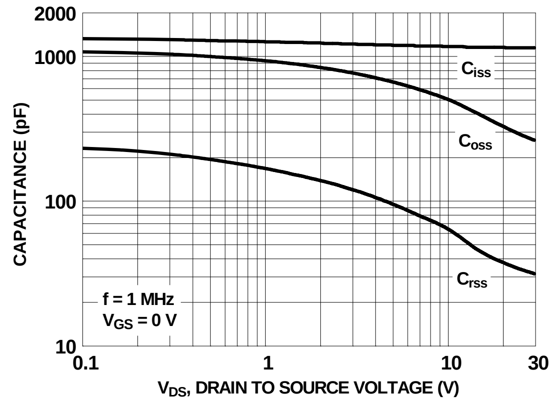


Figure 8. Capacitance vs Drain to Source Voltage

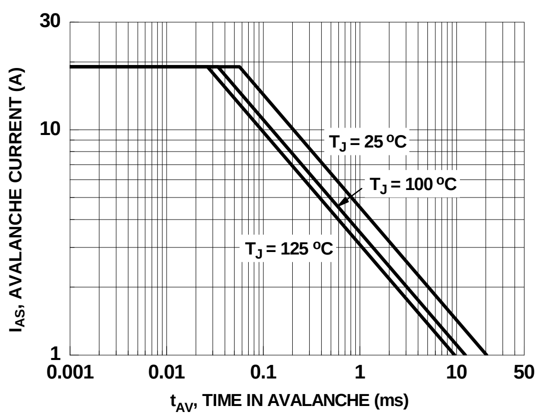


Figure 9. Unclamped Inductive Switching Capability

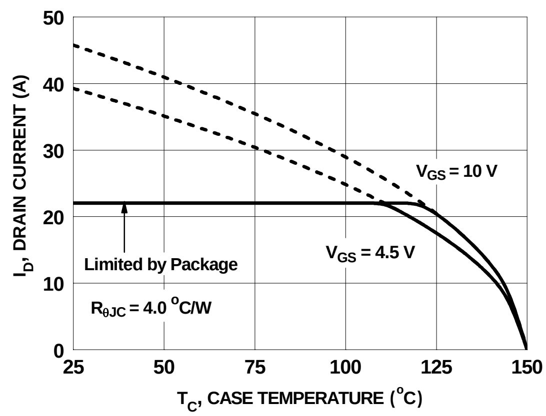


Figure 10. Maximum Continuous Drain Current vs Case Temperature

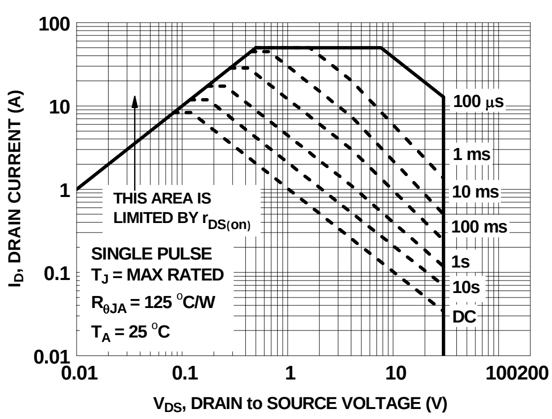


Figure 11. Forward Bias Safe Operating Area

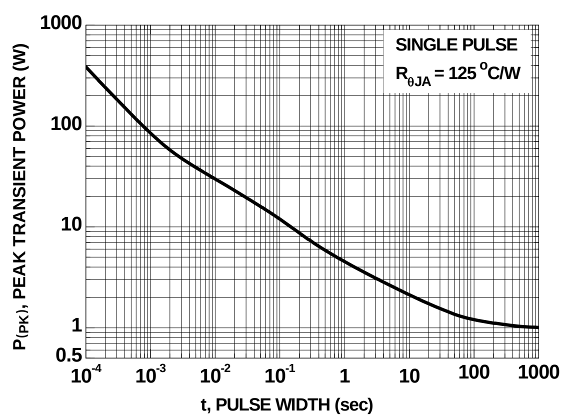


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

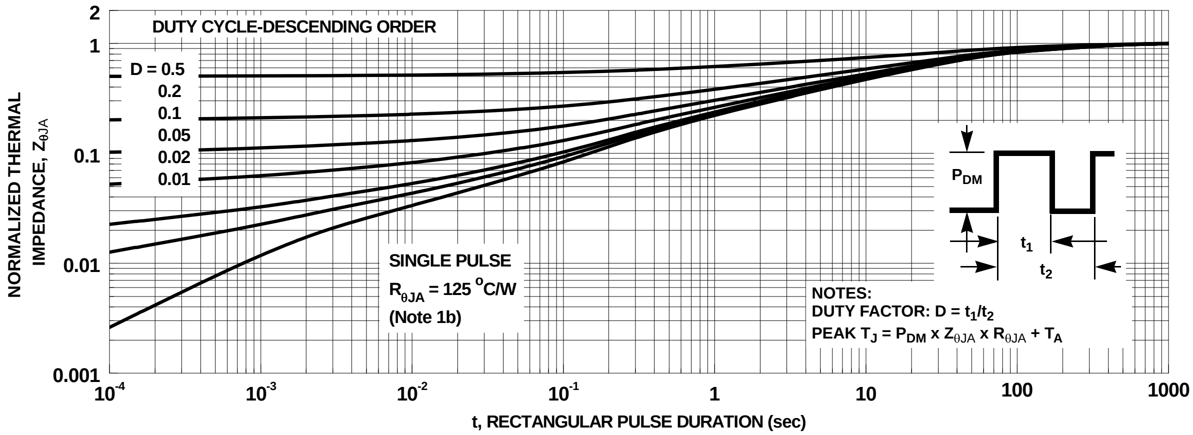


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted

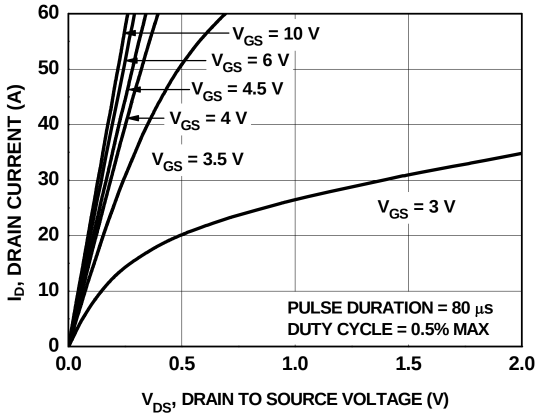


Figure 14. On-Region Characteristics

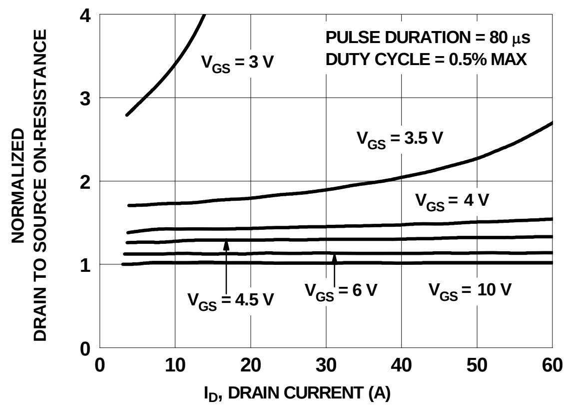


Figure 15. Normalized on-Resistance vs Drain Current and Gate Voltage

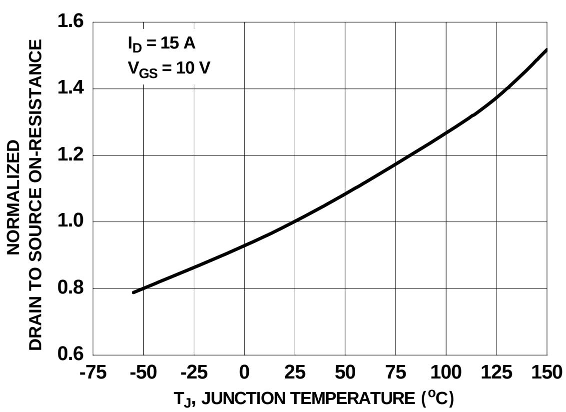


Figure 16. Normalized On-Resistance vs Junction Temperature

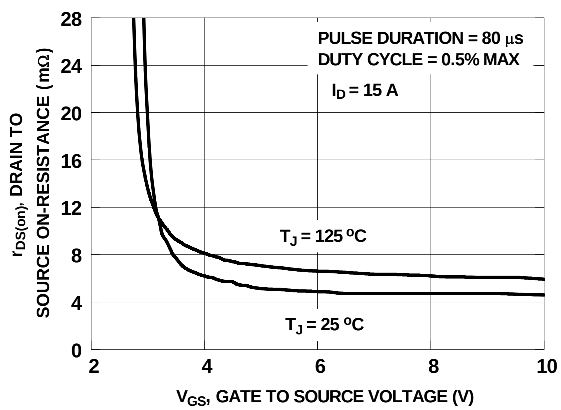


Figure 17. On-Resistance vs Gate to Source Voltage

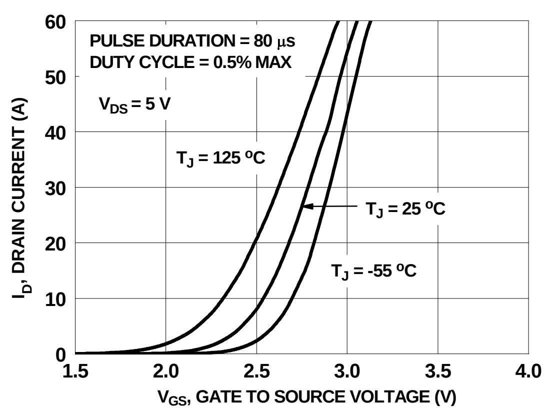


Figure 18. Transfer Characteristics

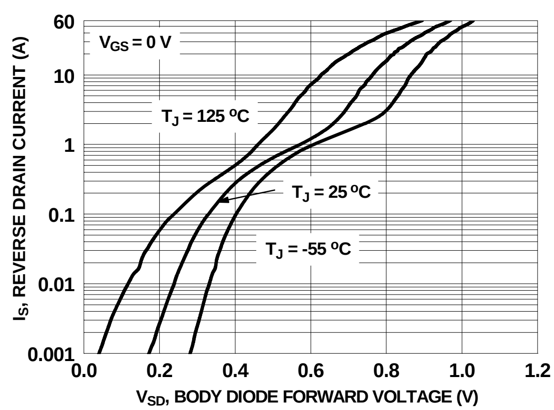


Figure 19. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q2 N-Channel) T_J = 25°C unless otherwise noted

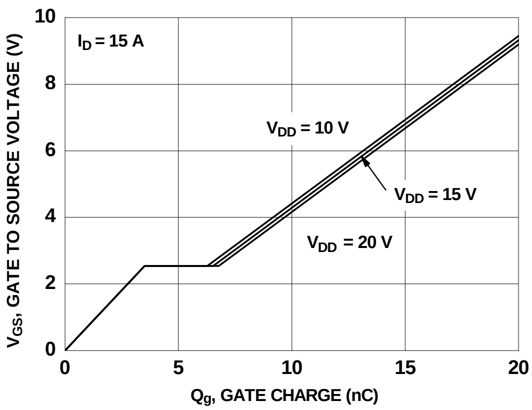


Figure 20. Gate Charge Characteristics

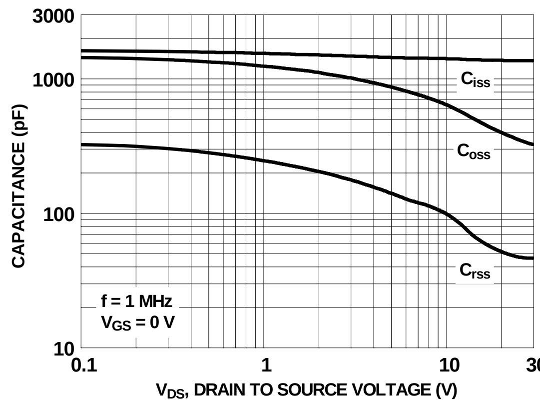


Figure 21. Capacitance vs Drain to Source Voltage

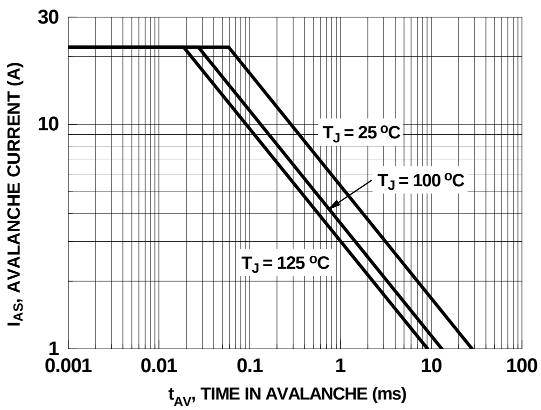


Figure 22. Unclamped Inductive Switching Capability

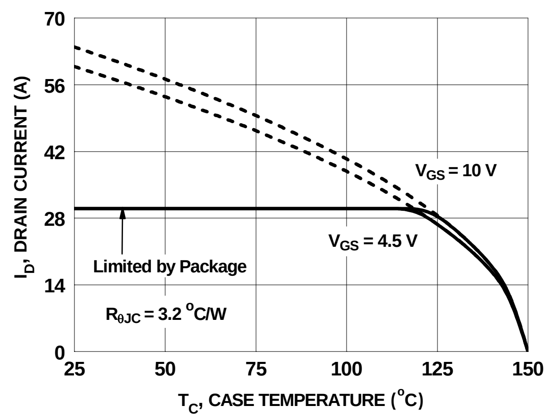


Figure 23. Maximum Continuous Drain Current vs Case Temperature

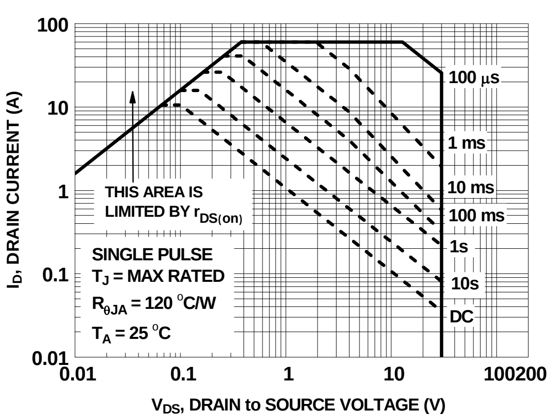


Figure 24. Forward Bias Safe Operating Area

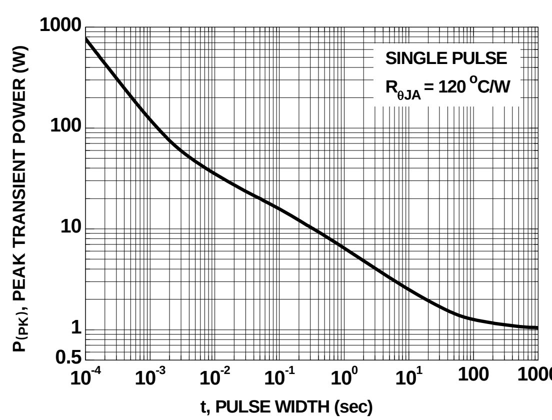


Figure 25. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted

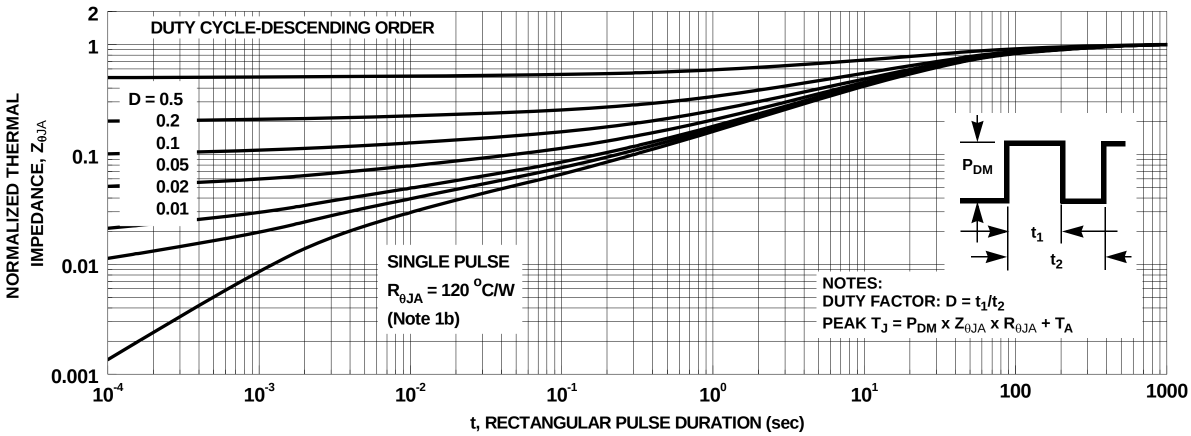


Figure 26. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET™ Schottky body diode Characteristics

Fairchild's SyncFET™ process embeds a Schottky diode in parallel with PowerTrench® MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverse recovery characteristic of the FDMS7608S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

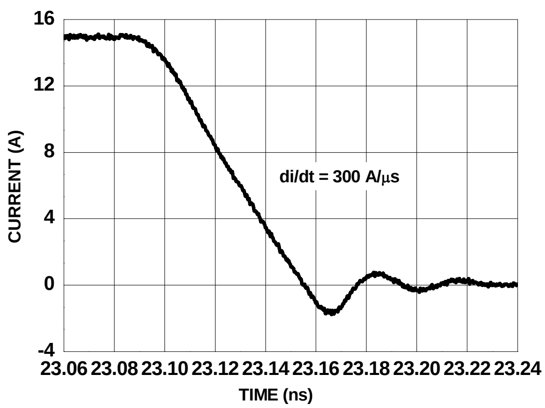


Figure 27. FDMS7608S SyncFET™ Body Diode Reverse Recovery Characteristic

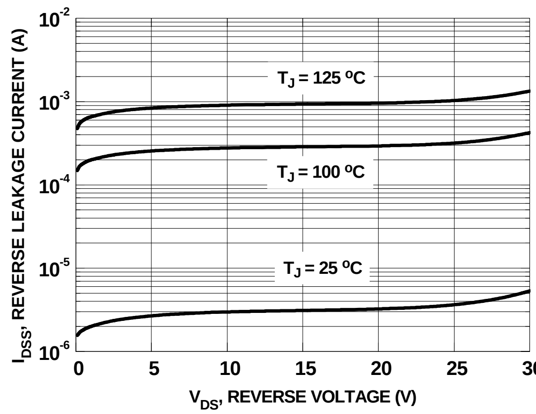
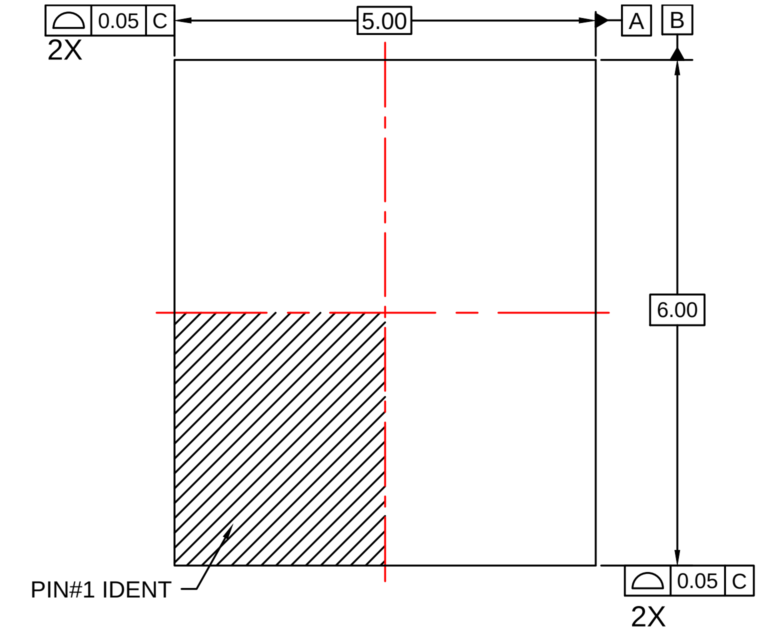
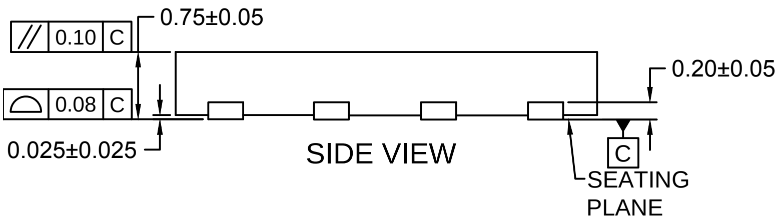
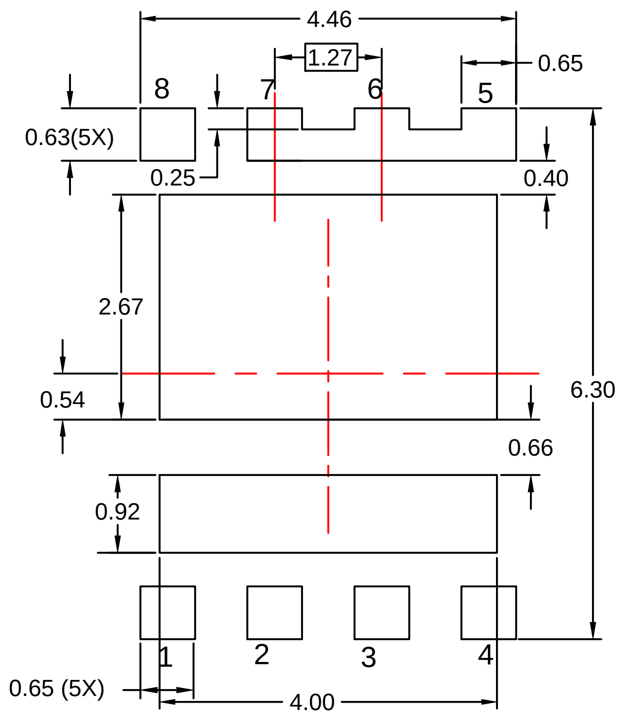


Figure 28. SyncFET™ Body Diode Reverse Leakage vs. Drain-Source Voltage

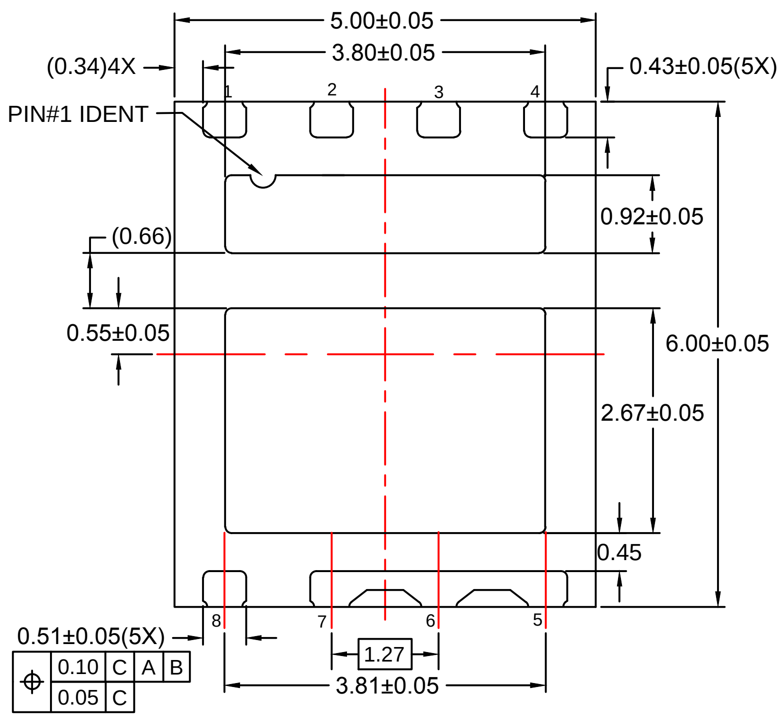




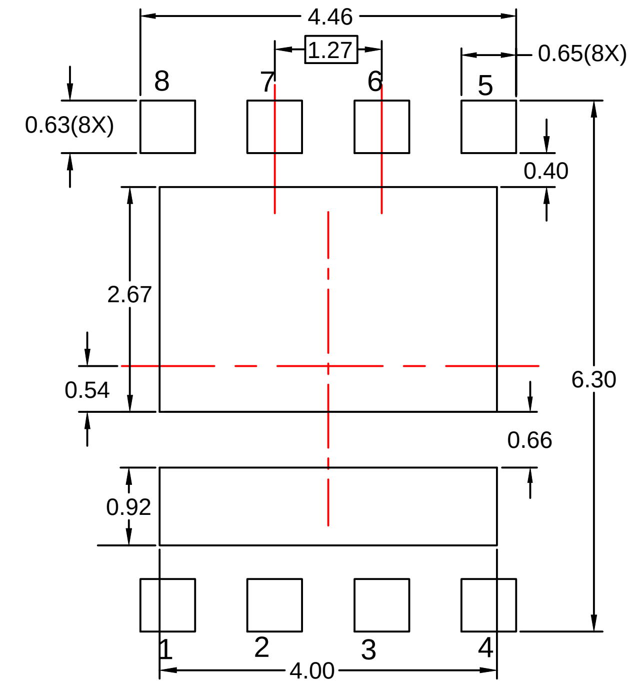
SIDE VIEW



RECOMMENDED LAND PATTERN
(OPTION 1 - FUSED LEADS 5,6,7)



BOTTOM VIEW



RECOMMENDED LAND PATTERN
(OPTION 2 - ISOLATED LEADS)

NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC STANDARD.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

E. DRAWING FILENAME: MKT-MLP08Prev2.

FAIRCHILD.

PUBLICATION ORDERING INFORMATION

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